L Number	Hits	Search Text	DB	Time stamp
-	12	(("6429063") or ("6417044") or ("6399441") or ("6395590") or ("6372564") or ("6346466") or ("6255166") or ("6583007") or ("6566203") or ("6555427") or ("6518125") or ("6482708")).PN.	USPAT	2003/10/15 14:43
-	2	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and (ono same (wet adj etching) same (dop$6 or implant$6) same (buried adj bit adj line))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:33
-	2	(ono same (wet adj etching) same (dop$6 or implant$6) same (buried adj bit adj line)) and ((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:12
-	3	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (wet adj etching) and (dop$6 or implant$6) and (buried adj bit adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:15
-	8	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (wet adj etching) and (dop$6 or implant$6) and (bit adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:27
-	94	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (dop$6 or implant$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:33
-	94	(((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (dop$6 or implant$6)) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:34
-	81	((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (dop$6 or implant$6)) and @ad<=20021115) and bit	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:29
-	72	((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (dop$6 or implant$6)) and @ad<=20021115) and (bit adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:34
-	2	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or nrom) and (ono same (wet adj etching) same (dop$6 or implant$6) same (buried adj bit adj line))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:33
-	157	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop$6 or implant$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:33
-	150	(((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop$6 or implant$6)) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:34
-	115	((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop$6 or implant$6)) and @ad<=20021115) and (bit adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:46
-	85	(((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop$6 or implant$6)) and @ad<=20021115) and (bit adj line)) and (etch$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:49

-	24	(((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop$6 or implant$6)) and @ad<=20021115) and (bit adj line)) and (wet adj etch$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:48
-	30	((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop$6 or implant$6)) and @ad<=20021115) and (bur$4 adj bit adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:47
-	6	((((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop$6 or implant$6)) and @ad<=20021115) and (bit adj line)) and (wet adj etch$5)) and (bur$4 adj bit adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:47
-	6	(((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop$6 or implant$6)) and @ad<=20021115) and (bur$4 adj bit adj line)) and (wet adj etch$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/02 14:49
-	26	(((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop$6 or implant$6)) and @ad<=20021115) and (bur$4 adj bit adj line)) and (etch$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 07:57
-	99	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or (NROM)) and ((ono or (oxide adj nitride adj oxide) or ((silicon adj oxide) adj (silicon adj nitride) adj (silicon adj oxide))) and (dop$6 or implant$6) and @ad<=20021115) and (bit adj line) and (word adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 10:52
-	1	("6566203").PN.	USPAT	2003/10/09 15:34
-	1	("6461906").PN.	USPAT	2003/09/03 13:17
-	1	("5496753").PN.	USPAT	2003/09/03 13:07
-	329	(438/261).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:07
-	1390	(438/257).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:09
-	578	(438/258).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:08
-	330	(438/259).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:08
-	98	(438/260).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:08
-	329	(438/261).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:08
-	199	(438/262).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:08

-	711	(438/526).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:09
-	694	(438/275).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:09
-	246	(438/294).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:10
-	152	(438/216).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:10
-	333	(438/591).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:10
-	152	(438/216).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:10
-	613	(438/264).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:11
-	636	(438/527).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:12
-	750	(438/287).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:12
-	74	(438/954).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 13:12
-	20	semiconductor same ono same (etch$4 adj stop)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 15:28
-	20	(semiconductor same ono same (etch$4 adj stop)) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 11:04
-	480	semiconductor and ono and (etch adj stop) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:21
-	12	438/287,261,591.ccls. and ono and (etch adj stop) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 11:06

-	264	438/287,261,591.ccls. and ono and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/03 15:38
-	397	257/$.ccls. and ono and (etch$3 adj stop$4 adj (layer or film)) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:52
-	340	438/$.ccls. and ono and (etch$3 adj stop$4 adj (layer or film)) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:52
-	502	ono and (etch$3 adj stop$4 adj (layer or film)) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:53
-	9	(ono same semiconductor same (etch$3 adj stop$4 adj (layer or film))) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:53
-	478	ono and semiconductor and (etch$3 adj stop$4 adj (layer or film)) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:34
-	32968	liu.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:36
-	10	liu.in. and cheng-jye	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:35
-	2054	hsiung.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:36
-	66294	chen.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:36
-	3	hsiung.in. and tai-liang	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:37
-	32	chen.in. and chia-hsing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 15:37
-	1	("6376341").PN.	USPAT	2003/10/10 11:29
-	3	(("6566203") or ("6461906") or ("5496753")).PN.	USPAT	2003/10/10 10:48
-	13	(("6429063") or ("6417044") or ("6399441") or ("6395590") or ("6372564") or ("6346466") or ("6255166") or ("6583007") or ("6566203") or ("6555427") or ("6518125") or ("6482708") or ("6376341")).PN.	USPAT	2003/10/15 14:49

-	14	(("6429063") or ("6417044") or ("6399441") or ("6395590") or ("6372564") or ("6346466") or ("6255166") or ("6583007") or ("6566203") or ("6555427") or ("6518125") or ("6482708") or ("6376341") or ("6538270")).PN.	USPAT	2003/10/16 09:22
-	2	(("6433384") or ("6472701")).PN.	USPAT	2004/07/19 13:20
-	65	("ONO") same (masking or protect$5) same ((silicon adj nitride) or ("SiN")) same (pattern$6 or (wet adj etch$6))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 09:47
-	63	("ONO") same (masking or protect$5) same ((silicon adj nitride) or ("SiN")) same (pattern$6 or (wet adj etch$6)) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 11:07
-	128	(semiconductor same ono same ((etch$4 adj stop) or (protect$6))) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 11:05
-	21	(semiconductor same ono same (etch$4 adj stop)) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 11:05
-	13	438/287,261,591.ccls. and ono and (etch adj stop) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 11:06
-	75	("ONO") same (masking or protect$5) same ((silicon adj nitride) or ("SiN")) same (pattern$6 or (wet adj etch$6)) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 11:07
-	83	(((oxide adj nitride adj oxide) or ("ONO")) same (masking or protect$5) same ((silicon adj nitride) or ("SiN")) same (pattern$6 or (wet adj etch$6))) and @ad<=20021115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/19 12:50
-	5	("5652173" | "5801100" | "6030877" | "6054329" | "6309922").PN.	USPAT	2004/07/19 12:41
-	5	("5652173" | "5801100" | "6030877" | "6054329" | "6309922").PN.	USPAT	2004/07/19 12:47
-	1	("5811315").PN.	USPAT	2004/07/19 13:20